

SEMICONDUCTOR TECHNICAL DATA

KDS114E

SILICON EPITAXIAL PLANAR DIODE

VHF TUNER BAND SWITCH APPLICATIONS.

FEATURES

· Small Package.

 $\cdot \ Small \ Total \ Capacitance : C_T \!\!=\!\! 1.2 pF(Max.).$

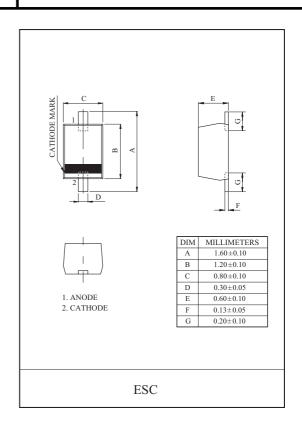
· Low Series Resistance : r_S =0.5 (Typ.).

• Suffix $\underline{\mathbf{U}}$: Qualified to AEC-Q101.

ex) KDS114E-RTK/HU

MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Reverse Voltage	V _R	35	V	
Forward Current	I_{F}	100	mA	
Power Dissipation	P_{D}	100	mW	
Junction Temperature	T _j	150		
Storage Temperature Range	T_{stg}	-55 150		



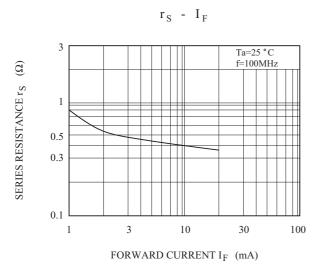
MARKING

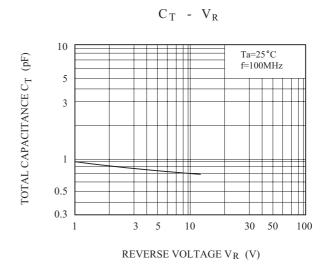


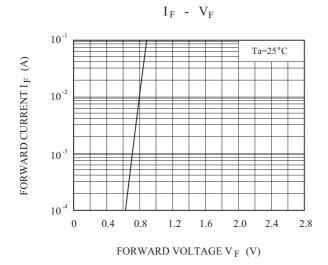
ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_{F}	I _F =2mA	-	-	0.85	V
Reverse Current	I_R	V _R =15V	-	-	0.1	μA
Reverse Voltage	V _R	I _R =1 µA	35	-	-	V
Total Capacitance	C_{T}	V _R =6V, f=1MHz	-	0.7	1.2	pF
Series Resistance	r _s	I _F =2mA, f=100MHz	-	0.5	0.9	

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Revision No: 4